L Number	Hits	Search Text	DB	Time stamp
- Namber	17	(sic or silicon adi carbide) near10 (CVD	USPAT;	2003/04/07 15:23
		or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		(etch near4 pits or nanotube)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/04/07 16:27
_	31	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/07 16:27
,		or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		impurity near10 pressure	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	9	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/07 16:29
-		or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		impurity near10 pressure near4 partial	EPO; JPO;	
		impulity neurro process	DERWENT;	
			IBM TDB	
	65	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/07 17:44
-	65	or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		pressure near4 partial same (silane or	EPO; JPO;	
		source or propane or silicon or carbon)	DERWENT;	
		source or propane of silicon of carbon,	IBM TDB	
		and impurity	USPAT;	2003/04/07 17:22
	23	(sic or silicon adj carbide) near10 (CVD	US-PGPUB;	
		or chemical adj vapor adj deposit\$4) and	EPO; JPO;	
		pressure near4 partial near10 (silane or	DERWENT;	
		source or propane or silicon or carbon)	IBM TDB	
	ļ	and impurity	USPAT;	2003/04/07 17:41
-	4	(sic or silicon adj carbide) near10 (CVD		2003/04/0/ 2/11
		or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		block\$4 near3 technique	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2003/04/07 17:42
_	16	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/07 17.42
		or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		block\$5 near10 impurit\$4	EPO; JPO;	
		-	DERWENT;	
			IBM_TDB	10.000
	17	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/07 17:50
_	1 - 1	or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		pressure near4 partial same (silane or	EPO; JPO;	
	İ	source or propane or silicon or carbon)	DERWENT;	
		and (impur\$4 or contain\$4 or dop\$4) near10	IBM_TDB	1
	1	partial adj pressure	_	
	4.0	1 1 1 1 1 1 1 1 1 1	USPAT;	2003/04/07 18:03
-	10	or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		pressure near4 partial near15 (silane or	EPO; JPO;	
		pressure heard partial hearts (strains of	DERWENT;	
		source or propane or silicon or carbon)	IBM_TDB	
		and (impur\$4 or contain\$4 or dop\$4) near10		
		partial adj pressure	USPAT;	2003/04/07 18:1
_	24	(sic or silicon adj carbide) near10 (CVD	US-PGPUB;	
		or chemical adj vapor adj deposit\$4) and	EPO; JPO;	
		pressure near4 partial near15 (silane or	DERWENT;	
		source or propane or silicon or carbon)		
		and (impur\$4 or contain\$4 or dop\$4) near10	1 TEM_TOB	
		(controls4 or adjust\$4 or prevent\$4)	1	2003/04/07 18:1
_	2	(sic or silicon adi carbide) nearlu (CVD	USPAT;	2003/04/07 2012
		or chemical adi vapor adi deposit\$4) and	US-PGPUB;	
		pressure near4 partial near15 (Sliane of	EPO; JPO;	
		source or propane or silicon or carbon)	DERWENT;	
		and impur\$4 same etch\$4	IBM_TDB	2002/04/07 10-1
	57	//sic or silicon adi carbide) near10 (CVD	USPAT;	2003/04/07 18:1
_	3'	or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		impur\$4 same etch\$4	EPO; JPO;	
		TIMPULY TOURG COOM!	DERWENT;	
			IBM_TDB	
		(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/07 18:1
_	27	or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		or chemical adj vapor adj deposicos, did	EPO; JPO;	
		impur\$4 near15 etch\$4	DERWENT;	
1	i	· ·	IBM TDB	1

	11	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/07 18:21
		or chemical adj vapor adj deposit\$4) and prevent\$4 near15 etch\$4 same pressure	US-PGPUB; EPO; JPO;	
		,	DERWENT; IBM TDB	
_	27	(sic or silicon adj carbide) near10 (CVD	USPĀT;	2003/04/08 12:08
	_	or chemical adj vapor adj deposit\$4) and	US-PGPUB; EPO; JPO;	
		impur\$4 near15 etch\$5	DERWENT;	
		(CVD	IBM_TDB USPAT;	2003/04/08 12:15
-	62	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and	US-PGPUB;	
		impur\$4 near15 (suppress\$4 or prevent\$4)	EPO; JPO; DERWENT;	
			IBM_TDB ·	
	26	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and	USPAT; US-PGPUB;	2003/04/08 12:33
		or chemical adj vapor adj depositiva, and impur\$4 near15 pressure	EPO; JPO;	
			DERWENT;	
	80	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/08 12:44
		or chemical adj vapor adj deposit\$4) and	US-PGPUB; EPO; JPO;	
		partial adj pressure and impur\$5	DERWENT;	
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB USPAT;	2003/04/08 12:48
-	45	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and	US-PGPUB;	2000,01,00
		micropipe	EPO; JPO; DERWENT;	
			IBM TDB	
_	16	(sic or silicon adj carbide) near10 (CVD	USPAT;	2003/04/08 14:21
		or chemical adj vapor adj deposit\$4) and (micropipe or etch adj pit) same (impur\$5)	US-PGPUB; EPO; JPO;	
		(micropipe of econ day pro, same vi	DERWENT;	
	20	(sic or silicon adj carbide) near5 (CVD or	IBM_TDB USPAT;	2003/04/08 14:36
•	30	chemical adi vapor adi deposit\$4) and	US-PGPUB;	
		partial adj pressure near13 (reactant or silane or propane or source)	EPO; JPO; DERWENT;	
			IBM_TDB USPAT;	2003/04/08 14:58
-	88	(sic or silicon adj carbide) near5 (CVD or chemical adj vapor adj deposit\$4) and rate	US-PGPUB;	2003/04/00 14:30
		same (etch near2 pit or defect)	EPO; JPO;	
			DERWENT; IBM TDB	
_	43	(sic or silicon adj carbide) near5 (CVD or	USPAT;	2003/04/08 15:37
		chemical adj vapor adj deposit\$4) and	US-PGPUB; EPO; JPO;	
		unintention\$5	DERWENT;	
		(chemical adj vapor adj deposit\$4 or CVD)	IBM_TDB USPAT;	2003/04/08 15:44
	7	and (impur\$5 same block\$4) same partial	US-PGPUB;	
		adj pressure	EPO; JPO; DERWENT;	
			IBM TDB	2003/04/08 15:49
_	12	(chemical adj vapor adj deposit\$4 or CVD)	USPAT; US-PGPUB;	2003/04/06 13.43
		and impur\$5 same block\$4 near10 pressure	EPO; JPO;	
			DERWENT; IBM TDB	
-		(chemical adj vapor adj deposit\$4 or CVD)	USPAT;	2003/04/08 15:53
-	1	and block\$4 near2 technique same impur\$5	US-PGPUB; EPO; JPO;	
			DERWENT;	
		nont hlocked and	IBM_TDB USPAT;	2003/04/10 10:11
-	5	partial adj pressure near15 block\$4 and (chemical adj vapor adj deposit\$4 or cvd)	US-PGPUB;	
		(5151115)	EPO; JPO; DERWENT;	
			IBM_TDB	

	4	partial adj pressure near15 impur\$4 near10 (prevent\$4 or suppress\$4) and (chemical	USPAT; US-PGPUB;	2003/04/10 10:15
		adj vapor adj deposit\$4 or cvd)	EPO; JPO; DERWENT; IBM TDB	
	29	pressure near15 impur\$4 near10 (prevent\$4 or suppress\$4) and (chemical adj vapor adj deposit\$4 or cvd)	USPĀT; US-PGPUB; EPO; JPO;	2003/04/10 10:26
	37	block\$4 near4 technique same (impur\$4 or	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/04/10 10:25
		dop\$4) and (chemical adj vapor adj deposit\$4 or cvd)	EPO; JPO; DERWENT; IBM TDB	
	25	<pre>pressure near15 dop\$4 near10 (prevent\$4 or suppress\$4) and (chemical adj vapor adj deposit\$4 or cvd)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/10 10:31
-	35	(chemical adj vapor adj deposit\$4 or cvd) and impurit\$4 near10 incorporat\$4 near10 pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/10 13:16
-	29	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/04/10 13:20
-	14	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane same silane	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/10 13:25
_	1	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane same silane same propane	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/10 13:26
-	4	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane and silane same propane	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/10 13:32
-	4	sic near10 (CVD or chemical adj vapor adj deposit\$4) and (tetramethylsilane or "Si(CH.sub.3).sub.4") and (silane or	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/10 13:34
-	26	"sih.sub.4") same (propane or "c.sub.3h.sub.8") sic near10 (CVD or chemical adj vapor adj deposit\$4) and (tetramethylsilane or "Si(CH.sub.3).sub.4") and (silane or "sih.sub.4")	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/10 13:3
-	61	a subido or eicl same	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/10 13:3
-	41	ibido or sicl same	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/04/10 13:5
_	29	"sih.sub.4") (heatif or thermal or temperature) near10	DERWENT; IBM_TDB USPAT;	2003/04/10 14:1
_	2:	rate same defects and (silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	

	44	(heat\$4 or thermal or temperature) near10	USPAT;	2003/04/10 14:38
_		rate near10 substrate same (sic or silicon	US-PGPUB;	
:		adi carbide) and (silicon adj carbide or	EPO; JPO;	
		sic) near5 (chemical adj vapor adj	DERWENT; IBM TDB	
		<pre>deposit\$4 or CVD) (heat\$4 or thermal or temperature) near10</pre>	USPAT;	2003/04/10 14:52
_	58	rate near10 (rapid\$4 or high\$4) same (sic	US-PGPUB;	
		or silicon adj carbide) and (silicon adj	EPO; JPO;	
		carbide or sic) near5 (chemical adj vapor	DERWENT;	
		adi deposit\$4 or CVD)	IBM_TDB	0000/04/10 14.50
-	2	(heat\$4 or thermal or temperature) near10	USPAT;	2003/04/10 14:59
		rate near10 ramp\$4 same (sic or silicon	US-PGPUB; EPO; JPO;	
		adj carbide) and (silicon adj carbide or sic) near5 (chemical adj vapor adj	DERWENT;	
		deposit\$4 or CVD)	IBM TDB	
_	18		USPAT;	2003/04/10 15:05
_		rate near10 ramp\$4 and (silicon adj	US-PGPUB;	
		carbide or sic) near5 (chemical adj vapor	EPO; JPO;	
		adj deposit\$4 or CVD)	DERWENT;	
		(tal analysis on sigl poor5	IBM_TDB USPAT;	2003/04/10 15:08
_	24	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and ramp\$4 near3 rate	EPO; JPO;	
		and rampys nears race	DERWENT;	
	1		IBM_TDB	0000404410 15 10
_	72	(silicon adj carbide or sic) near5	USPAT;	2003/04/10 15:10
	1	(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and rate near10 (deposit\$4) near4	EPO; JPO; DERWENT;	
		temperature	IBM TDB	
	20	(silicon adj carbide or sic) near5	USPAT;	2003/04/10 15:16
-	38	(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and rate near10 (deposit\$4) near4	EPO; JPO;	
		temperature same (silicon adj carbide or	DERWENT;	
		(sic)	IBM_TDB	2003/04/10 15:26
_	3	(silicon adj carbide or sic) near5	USPAT; US-PGPUB;	2003/04/10 13.20
		(chemical adj vapor adj deposit\$4 or	EPO; JPO;	
		CVD).ti. and (heat\$4 near4 rate)	DERWENT;	
			IBM TDB	
	7	(silicon adj carbide or sic) near5	USPAT;	2003/04/10 15:25
-	′	/chemical adi vapor adi deposit\$4 or	US-PGPUB;	
		CVD).ti. and rate near10 (rapid\$4 or high)	EPO; JPO;	
			DERWENT; IBM TDB	
	1		USPAT;	2003/04/10 15:25
-	11	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or	US-PGPUB;	
		(chemical adj vapor adj deposity of CVD).ti. and rate near5 (temperature or	EPO; JPO;	-
		thermal)	DERWENT;	
			IBM_TDB	0002/04/10 15:36
_	16	(silicon adj carbide or sic) near5	USPAT;	2003/04/10 15:39
		(chemical adi vapor adi deposits4 or CVD)	US-PGPUB; EPO; JPO;	
		and (heating near5 rate) same deposit\$4	DERWENT;	
			IBM TDB	
		, in an add combide or sign nears	USPAT;	2003/04/14 10:50
-	84	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (heating near5 rate) same temperature	EPO; JPO;	
		and modeling induction	DERWENT;	
			IBM TDB	2003/04/14 11:18
_	81	(silicon adj carbide or sic) near5	USPAT; US-PGPUB;	2003/04/14 11:16
		(chemical adi vapor adi deposits4 or CVD)	EPO; JPO;	
		and (rate) near5 temperature near10	DERWENT;	
		(heat\$3 or ramp\$4)	IBM TDB	
	59	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:2:
-	39	(chemical adi vapor adi deposits4 or CVD)	US-PGPUB;	
		and (rate) near5 temperature near10	EPO; JPO;	
		(heat\$3 or ramp\$4)	DERWENT; IBM TDB	
1	- 1		TDM IDD	

-	13	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:23
		(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (rate) near5 thermal near10 (heat\$3 or	EPO; JPO;	
		ramp\$4)	DERWENT;	_
		•	IBM TDB	•
_	12	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:27
		(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
Ì		same (rate) near5 (heat\$3 or ramp\$4)	EPO; JPO;	
		,	DERWENT;	
			IBM TDB	
	15	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:31
_	4.0	(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (rate) near5 (heat\$3 or ramp\$4) same	EPO; JPO;	
			DERWENT;	
		(silicon adj carbide or sic)		
			IBM_TDB	2003/04/14 11:34
-	11	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:34
		(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (rate) near5 (heat\$3 or ramp\$4) near4	EPO; JPO;	
		(min or minute)	DERWENT;	
			IBM_TDB	
_	41	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:39
		(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (rate) near6 (min or minute) near3 C	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	56	(silicon adj carbide or sic) near2	USPĀT;	2003/04/14 11:44
		(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (rate) near3 C! same (sic or silicon	EPO; JPO;	
		adj carbide)	DERWENT;	
		adj carbrac,	IBM TDB	
	11	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:47
_	11	(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (rate) near3 C! and 117/84-109.ccls.	EPO; JPO;	
	1	and trace, hears c. and river residers.	DERWENT;	
			IBM TDB	
1	_	(-ili adi mambido om gia) noam?	USPAT;	2003/04/14 11:51
-	7	(silicon adj carbide or sic) near2	US-PGPUB;	2000,01,11 11.01
		(chemical adj vapor adj deposit\$4 or CVD)	EPO; JPO;	
		and (rate) near3 (heat\$4 or ramp\$4) and		
		117/84-109.ccls.	DERWENT;	
	-		IBM_TDB	2002/04/14 11:51
-	23	(silicon adj carbide or sic) near2	USPAT;	2003/04/14 11:51
		(chemical adj vapor adj deposit\$4 or CVD)	US-PGPUB;	
		and (rate) near3 (temperature) and	EPO; JPO;	
		117/84-109.ccls.	DERWENT;	
]		IBM_TDB	1